

**Product data sheet** 

### 1. General description

Ultrafast, dual common cathode, epitaxial rectifier diodes in a SOT428 (DPAK) plastic package.

#### 2. Features and benefits

- Fast switching
- Low thermal resistance
- Soft recovery characteristic
- Low forward voltage drop
- Reverse surge capability
- High thermal cycling performance

### 3. Applications

• Output rectifiers in high-frequency switched-mode power supplies

### 4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter	Conditions	Values				Unit
Absolute	maximum rating						
$V_{\text{RRM}}$	repetitive peak reverse voltage			2	200		V
I <sub>O(AV)</sub>	average output current	δ = 0.5; square-wave pulse; T <sub>mb</sub> ≤ 119 °C; both diodes conducting; <u>Fig. 5</u> ; <u>Fig. 6</u>		10			A
I <sub>FRM</sub>	repetitive peak forward current	δ = 0.5; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 119 °C; square-wave pulse; per diode		10			А
I <sub>FSM</sub>	non-repetitive peak	t <sub>p</sub> = 10 ms; sine-wave pulse; per diode	50			А	
forward current		$t_p$ = 8.3 ms; sine-wave pulse; per diode	55			А	
Symbol	Parameter	Conditions	Min Typ Max		Unit		
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 2</u>		-	0.95	1.1	V
		I <sub>F</sub> = 5 A; T <sub>j</sub> = 150 °C; <u>Fig. 2</u>		-	0.8	0.895	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 2</u>		-	1.1	1.25	V
Dynamic	characteristics			1			
t <sub>rr</sub>	reverse recovery time	ramp recovery; $I_F = 1 A$ ; $V_R = 30 V$ ; $dI_F/dt = 100 A/\mu s$ ; $T_j = 25 °C$ ; Fig. 3		-	15	25	ns
		step recovery; when switched from $I_F = 0.5 A$ to $I_R = 1 A$ ; measured at $I_R = 0.25 A$		-	10	20	ns

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## 5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		
2	K	cathode [1]		
3	A2	anode 2		
mb	К	mounting base; connected to cathode		K sym125

[1] It is not possible to connect to pin 2 of the SOT428 package.

## 6. Ordering information

Table 3. Ordering information						
Type number	Package	ge				
	Name	Description	Version			
BYQ28ED-200	DPAK	plastic single-ended surface-mounted package (DPAK); 3-leads (one lead cropped)	SOT428			

## 7. Marking

Table 4. Marking codes						
	Type number	Marking codes				
	BYQ28ED-200	BYQ28ED-200				

## 8. Limiting values

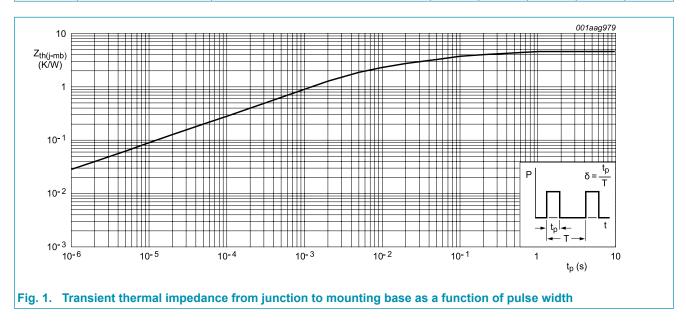
#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{\text{RRM}}$	repetitive peak reverse voltage		200	V
$V_{\text{RWM}}$	crest working reverse voltage		200	V
V <sub>R</sub>	reverse voltage	$\delta$ = 1.0; square-wave pulse;	200	V
I <sub>O(AV)</sub>	average output current	δ = 0.5; square-wave pulse; T <sub>mb</sub> ≤ 119 °C; both diodes conducting; <u>Fig. 5; Fig. 6</u>	10	A
I <sub>FRM</sub>	repetitive peak forward current	δ = 0.5; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 119 °C; square-wave pulse; per diode	10	A
I <sub>FSM</sub>	non-repetitive peak	$t_p$ = 10 ms; sine-wave pulse; per diode	50	A
forward	forward current	$t_p$ = 8.3 ms; sine-wave pulse; per diode	55	А
I <sub>RM</sub>	peak reverse recovery current	$δ = 0.001; t_p = 2 μs$	0.2	A
I <sub>RSM</sub>	non-repetitive peak reverse current	t <sub>p</sub> = 100 μs	0.2	A
T <sub>stg</sub>	storage temperature		-40 to 150	°C
Tj	junction temperature		150	°C
Electrosta	tic discharge		1	1
V <sub>ESD</sub>	electrostatic discharge voltage	all pins; human body model; C = 250 pF; R = 1.5 k $\Omega$	8	kV

### 9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to	with heatsink compound; both diodes conducting	-	-	3	K/W
mo	mounting base	with heatsink compound; per diode; <u>Fig 1</u>	-	-	4.5	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W



## **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics	· · · · · · · · · · · · · · · · · · ·				
V <sub>F</sub>	forward voltage	brward voltage $I_F = 5 \text{ A}; T_j = 150 \text{ °C}; Fig. 2$		0.8	0.895	V
		I <sub>F</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 2</u>	-	0.95	1.1	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 2</u>	-	1.1	1.25	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 200 V; T <sub>j</sub> = 25 °C	-	2	10	μA
		V <sub>R</sub> = 200 V; T <sub>j</sub> = 100 °C	-	0.1	0.2	mA
Dynamic	characteristics					
Q <sub>r</sub>	recovered charge	I <sub>F</sub> = 2 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 20 A/μs; T <sub>j</sub> = 25 °C; <u>Fig. 3</u>	-	4	9	nC
t <sub>rr</sub>	reverse recovery time	ramp recovery; I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 100 A/µs; T <sub>j</sub> = 25 °C; <u>Fig. 3</u>	-	15	25	ns
		step recovery; when switched from $I_F = 0.5 A$ to $I_R = 1 A$ ; measured at $I_R = 0.25 A$	-	10	20	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 5 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 3}$	-	0.5	0.7	A
$V_{FR}$	forward recovery voltage	I <sub>F</sub> = 1 A; dI <sub>F</sub> /dt = 10 A/μs; T <sub>i</sub> = 25 °C; <u>Fig. 4</u>	-	1	-	V

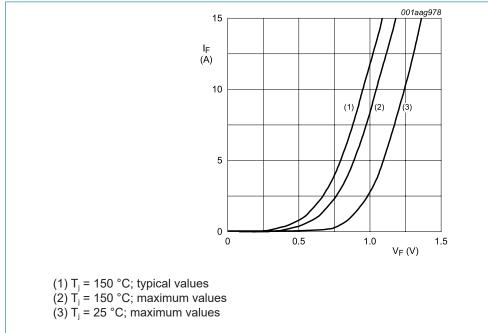
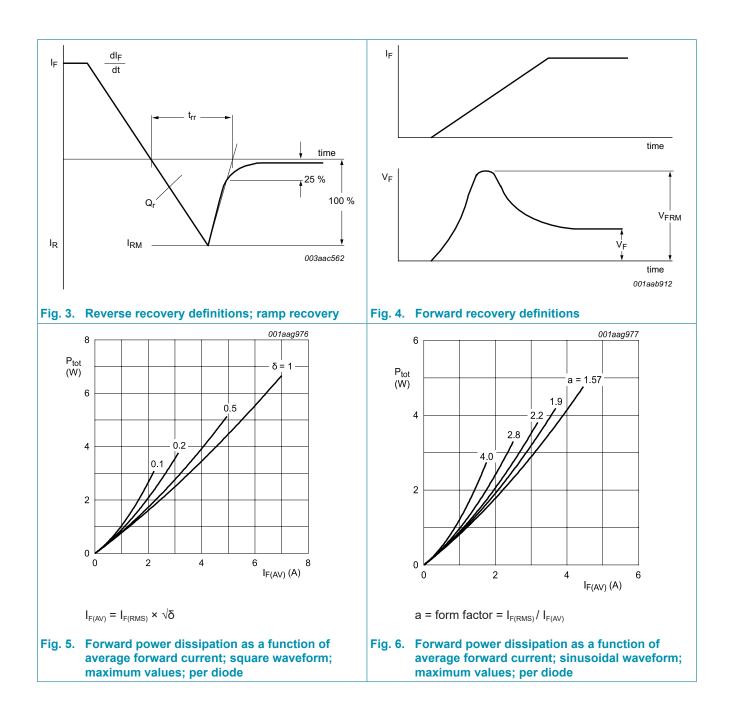


Fig. 2. Forward current as a function of forward voltage

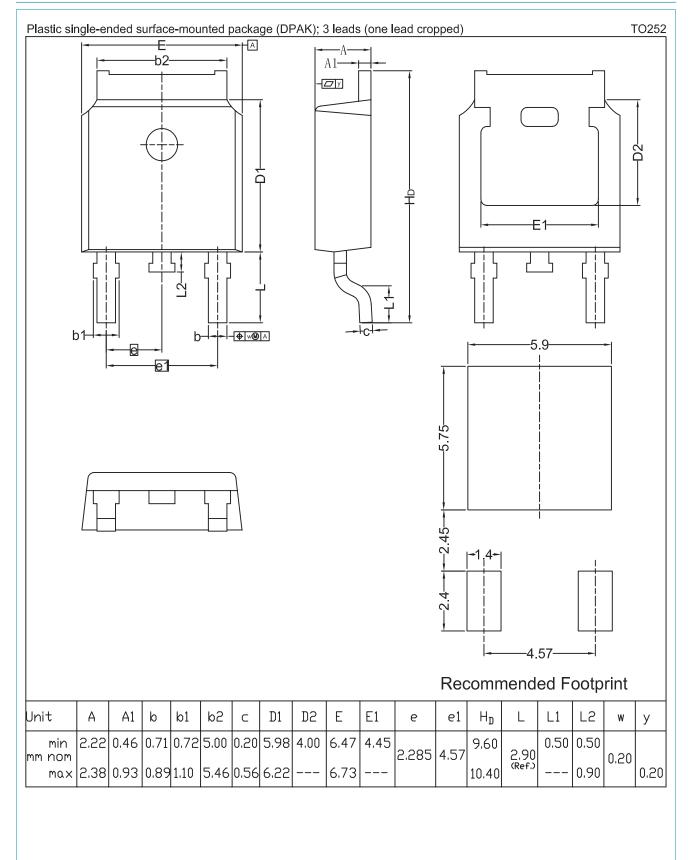
### **BYQ28ED-200**

Rectifier diodes ultrafast, rugged



#### **BYQ28ED-200** Rectifier diodes ultrafast, rugged

## 11. Package outline



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BYQ28ED-200

## **12. Revision history**

Table 8. Revision histor	ry						
Document ID	Release date	Data sheet status	Change notice	Supersedes			
BYQ28ED-200 v.5	20180224	Product data sheet	-	BYQ28_SER_E_ED_4			
Modifications: Ch	ange from NXP version to We	eEn version					
BYQ28_SER_E_ED_4	20071205	Product data sheet	-	BYQ28E_SERIES_3			
<ul> <li>Modifications:</li> <li>The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> <li>Limiting values table: some parameter descriptions amended to conform to latest standards; IFRM conditions amended; VESD row added.</li> <li>Characteristics: Qrr changed to Qr 'recovered charge'; trr1 and trr2 changed to trr with 'ramp recovery' and 'step recovery' added to conditions.</li> </ul>							
BYQ28E_SERIES_3	19981001	Product specification	-	BYQ28E_SERIES_2			
BYQ28E_SERIES_2	19980701	Product specification	-	BYQ28E_SERIES_1; BYQ28EB_SERIES_1			
BYQ28E_SERIES_1; BYQ28EB_SERIES_1	19960801	Product specification	-	-			

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## 13. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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